

• General Description

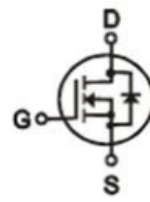
The ZM098N06D combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

• Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

• Application

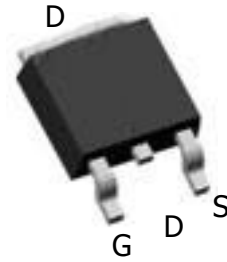
- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

• Product Summary


$V_{DS}=60V$

$R_{DS(ON)}=9.8m\Omega$

$I_D=50A$


TO-252
• Ordering Information:

Part NO.	ZM098N06D
Marking	ZM098N06
Packing Information	REEL TAPE
Basic ordering unit (pcs)	2500

• Absolute Maximum Ratings ($T_C=25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	20	V
Continuous Drain Current	$I_D@TC=25^\circ C$	50	A
	$I_D@TC=75^\circ C$	38	A
	$I_D@TC=100^\circ C$	31.5	A
Pulsed Drain Current ^①	I_{DM}	104	A
Total Power Dissipation($TC=25^\circ C$)	$P_D@TC=25^\circ C$	70	W
Total Power Dissipation($TA=25^\circ C$)	$P_D@TA=25^\circ C$	2.8	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ C$
Storage Temperature	T_{STG}	-55 to 150	$^\circ C$
Avalanche Current	I_{AS} I_{AR}	40	A

•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	1.8	$^{\circ}C/W$
Thermal resistance, junction - ambient	R_{thJA}	-	-	45	$^{\circ}C/W$
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	$^{\circ}C$

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	60			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.0	1.6	2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=24A$		9.8	13	$m\Omega$
		$V_{GS}=4.5V, I_D=12A$		14	18	$m\Omega$
Forward Transconductance	g_{FS}	$V_{DS}=25V, I_D=10A$		30		S
Source-drain voltage	V_{SD}	$I_S=24A$			1.28	V

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	$f = 1MHz$	-	3220	-	pF
Output capacitance	C_{oss}		-	149	-	
Reverse transfer capacitance	C_{rss}		-	106	-	

•Gate Charge characteristics($T_a=25^{\circ}C$)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q_g	$V_{DD}=25V$	-	30	-	nC
Gate - Source charge	Q_{gs}	$I_D=8A$	-	9	-	
Gate - Drain charge	Q_{gd}	$V_{GS}=10V$	-	15	-	

Note: ① Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$;

Fig.1 Power Dissipation

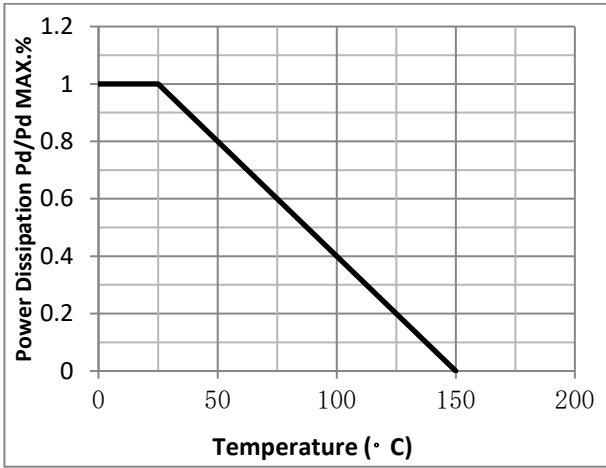


Fig.2 Typical output Characteristics

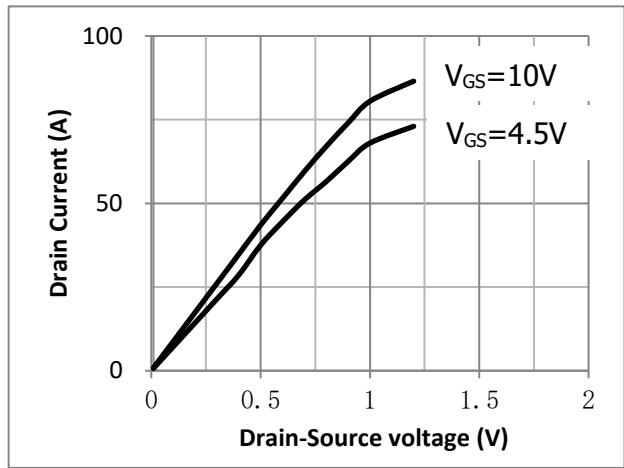


Fig.3 Threshold Voltage V.S Junction Temperature

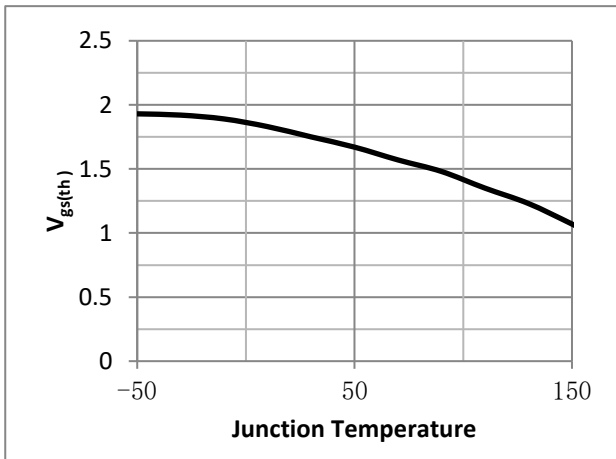


Fig.4 Resistance V.S Drain Current

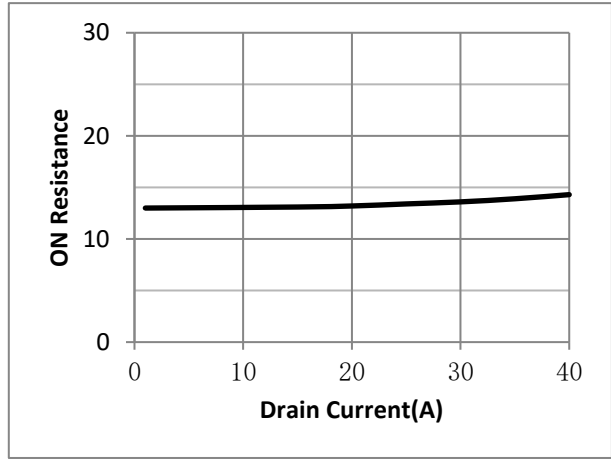


Fig.5 On-Resistance VS Gate Source Voltage

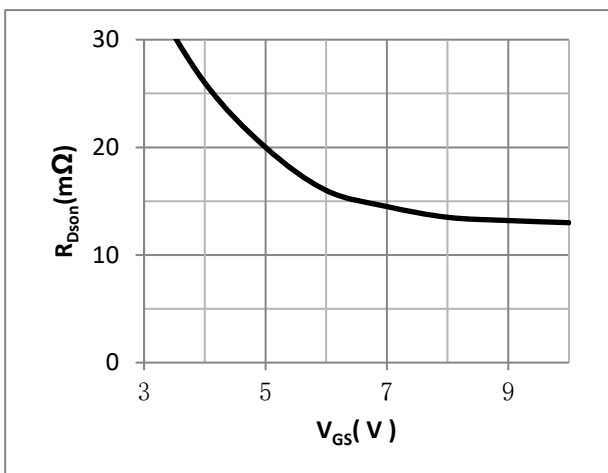


Fig.6 On-Resistance V.S Junction Temperature

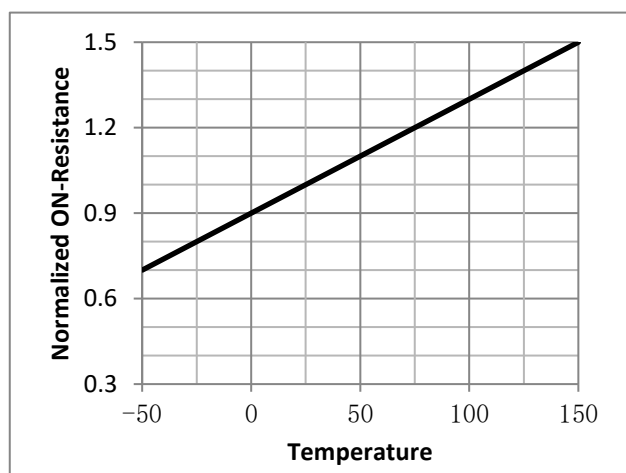


Fig.7 Switching Time Measurement Circuit

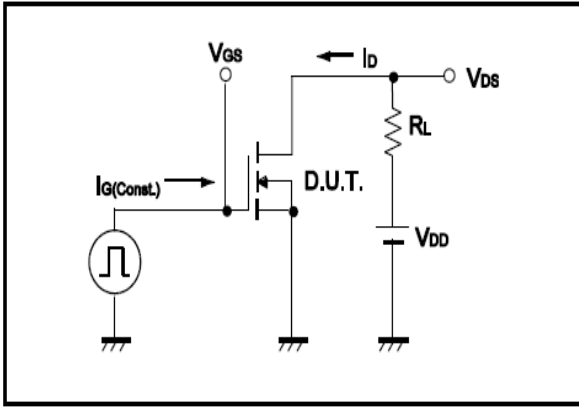


Fig.8 Gate Charge Waveform

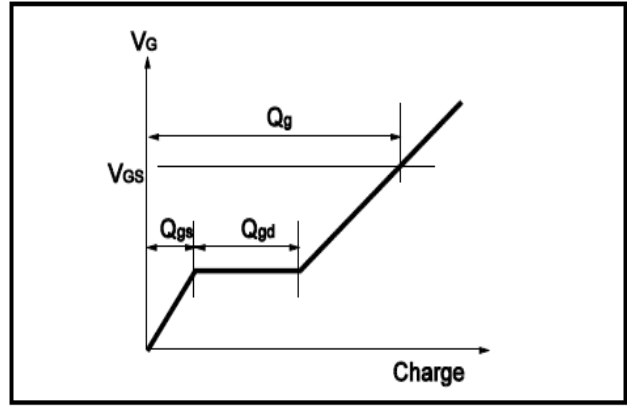


Fig.9 Switching Time Measurement Circuit

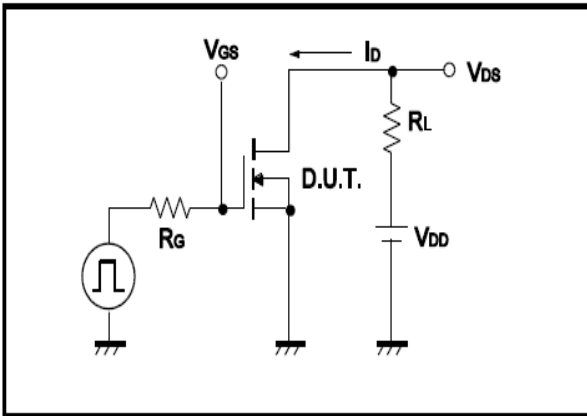


Fig.10 Gate Charge Waveform

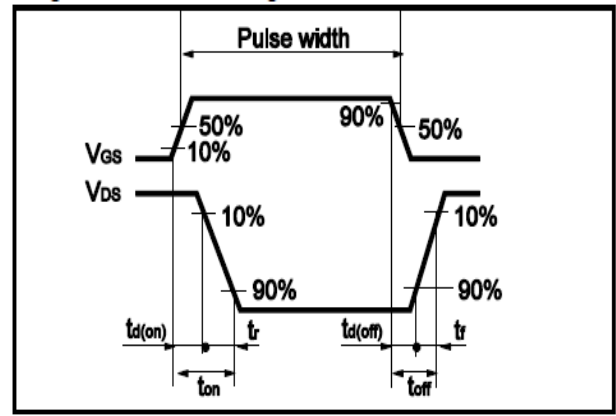


Fig.11 Avalanche Measurement Circuit

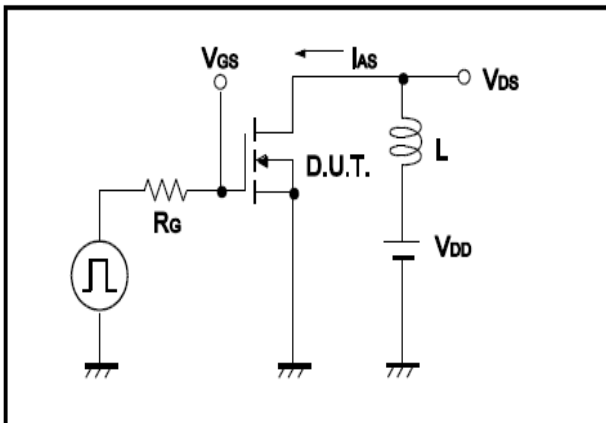
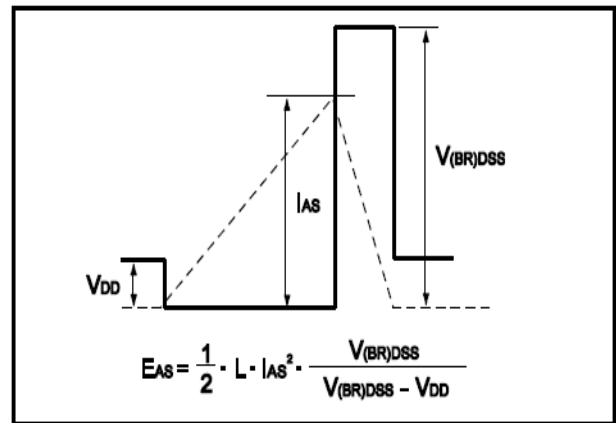


Fig.12 Avalanche Waveform



•Dimensions(TO-252)

Unit: mm

SYMBOL	min	max	SYMBOL	min	max
A	2.10	2.50	B	0.85	1.25
b	0.50	0.80	b1	0.50	0.90
b2	0.45	0.70	C	0.45	0.70
D	6.30	6.75	D1	5.10	5.50
E	5.30	6.30	e1	2.25	2.35
L1	9.20	10.60	e2	4.45	4.75
L2	0.90	1.75	L3	0.60	1.10
K	0.00	0.23			

